



STH180N10F3-2 Information



For Reference Only

Part Number STH180N10F3-2
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 120A H2PAK **Package** TO-263-3, D2Pak (2 Leads + Tab) Variant

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STH180N10F3-2 Specifications

Manufacturer Part Number STH180N10F3-2 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab) Variant Series STripFET? III FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 180A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 114.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6665pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 315W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant Report errors?		
CategoryDiscrete Semiconductor ProductsPackageTO-263-3, D2Pak (2 Leads + Tab) VariantSeriesSTripFET? IIIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C180A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs114.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6665pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 60A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	Manufacturer Part Number	STH180N10F3-2
Package TO-263-3, D2Pak (2 Leads + Tab) Variant Series STripFET? III FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 180A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 114.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6665pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 315W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Manufacturer	STMicroelectronics
Package TO-263-3, D2Pak (2 Leads + Tab) Variant Series STripFET? III FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 180A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 114.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6665pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 315W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case Too 250 AMOS 100 AC	Category	Discrete Semiconductor Products
SeriesSTripFET? IIIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C180A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs114.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6665pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 60A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 180A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 114.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case NOSFET (Metal Oxide) 100V 100V 6665PE (250µA 45 mOhm @ 60A, 10V -55°C ~ 175°C (TJ) Surface Mount TO-263-3, D2Pak (2 Leads + Tab) Variant	Package	TO-263-3, D2Pak (2 Leads + Tab) Variant
Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 180A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 114.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6665pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Series	STripFET? III
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C180A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs114.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6665pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 60A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 114.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature Supplier Device Package H2PAK Package / Case 180A (Tc) 180A (Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs114.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6665pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 60A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	180A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 6665pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 60A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	Gate Charge (Qg) (Max) @ Vgs	114.6nC @ 10V
FET Feature - Power Dissipation (Max) 315W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Input Capacitance (Ciss) (Max) @ Vds	6665pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 60A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs4.5 mOhm @ 60A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Power Dissipation (Max)	315W (Tc)
Mounting Type Surface Mount Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Rds On (Max) @ Id, Vgs	4.5 mOhm @ 60A, 10V
Supplier Device Package H2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Mounting Type	Surface Mount
	Supplier Device Package	H2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab) Variant
		Report errors?

STH180N10F3-2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STH180N10F3-2 Payment Methods



















STH180N10F3-2 Shipping Methods













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